

using crystalline silicon and gallium arsenide cells as examples. Chapter 8 deals with thin film photovoltaic materials, discussing physical processes and design issues relevant to thin films and focusing on the ways in which the standard model must be adapted for thin film devices. Chapter 9 deals with various techniques for managing light in order to maximise performance, and Chapter 10 covers a range of approaches, mainly theoretical, to increasing the efficiency of solar cells above the limit for a single band gap photoconverter.

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This book is dedicated to the memory of Stephen Robinson and M.V. McCaughan.

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